MSKSEMI 美森科













ESD

TV

TSS

MOV

GDT

PLED

MMST3904

Product specification

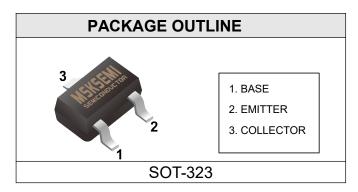




FEATURES

Complementary to MMST3906

Reference News



MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

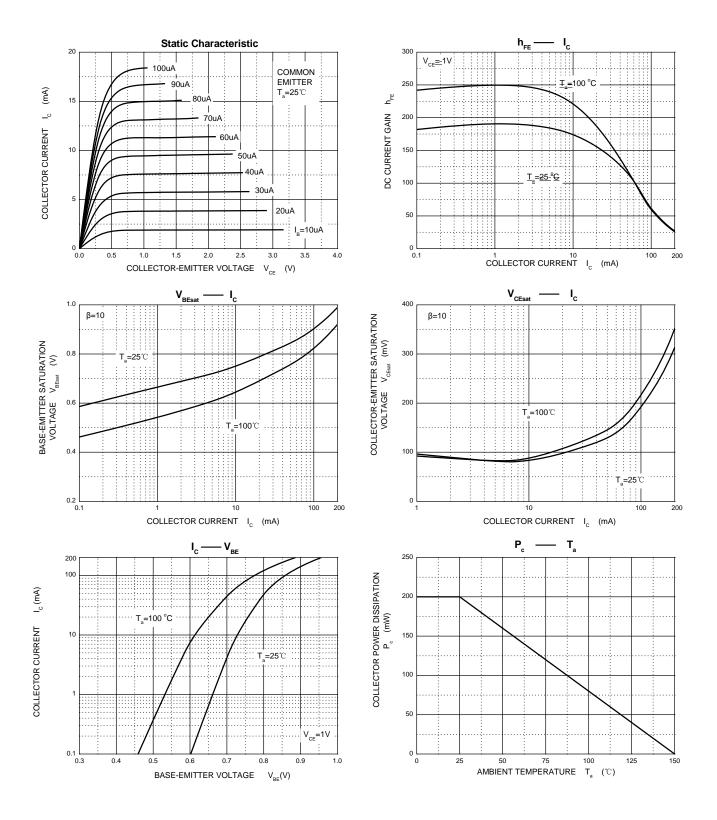
Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage	60	V
Vceo	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5	V
lc	Collector Current	200	mA
Pc	Collector Power Dissipation	200	mW
Roja	Thermal Resistance From Junction To Ambient	625	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO} *	l _C =10μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	Ic=1mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO} *	I _E =10μA, I _C =0	5			V
Collector cut-off current	I _{CBO} *	V _{CB} =60V, I _E =0			60	nA
Collector cut-off current	ICEX	V _{CE} =30V, V _{BE(off)} =3V			50	nA
	h _{FE} *	V _{CE} =1V, I _C =100μA	40			
		V _{CE} =1V, I _C =1mA	70			
DC current gain		V _{CE} =1V, I _C =10mA	100		300	
		V _{CE} =1V, I _C =50mA	60			
Q-IIt	V _{CE(sat)} *	I _C =10mA, I _B =1mA			0.25	V
Collector-emitter saturation voltage		I _C =50mA, I _B =5mA			0.3	V
D	V _{BE(sat)} *	I _C =10mA, I _B =1mA			0.85	V
Base-emitter saturation voltage		lc=50mA, I _B =5mA			0.95	V
Transition frequency	f⊤	V _{CE} =20V,I _C =10mA , f=100MHz	300			MHz
Collector output capacitance	Cob	V _{CB} =5V, I _E =0, f=1MHz			4	pF
Collector output capacitance	C_{ib}	V _{EB} =0.5V, I _E =0, f=1MHz			8	pF
Delay time	t _d	V _{CC} =3V, V _{BE(off)} =0.5V			35	ns
Rise time	tr	I _C =10mA, I _{B1} =1mA			35	ns
Storage time	ts	\\3\\ 10m \\			225	ns
Fall time	t _f	V _{CC} =3V, I _C =10mA, I _{B1} = I _{B2} =1mA			75	ns

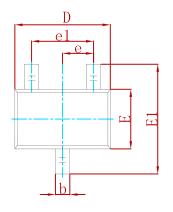
^{*}Pulse test: pulse width ≤300µs,duty cycle≤ 2.0%.

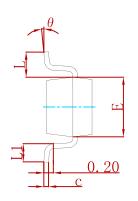


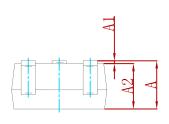




PACKAGEMECHANICALDATA

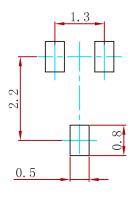






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMST3904	SOT-323	3000



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